

NPN General Purpose Amplifier

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1µ to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		PN2484	*MMBT2484	
PD	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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NPN General Purpose Amplifier (continued)

Electri	Electrical Characteristics TA = 25°C unless otherwise noted				
Symbol	Parameter	Test Conditions	Min	Max	Units

OFF CHARACTERISTICS

BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm B} = 0$	60		V
BV _{CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10$ mA, $I_{\rm E} = 0$	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	6.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 45 \text{ V}, I_E = 0$ $V_{CB} = 45 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$		10 10	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		10	nA

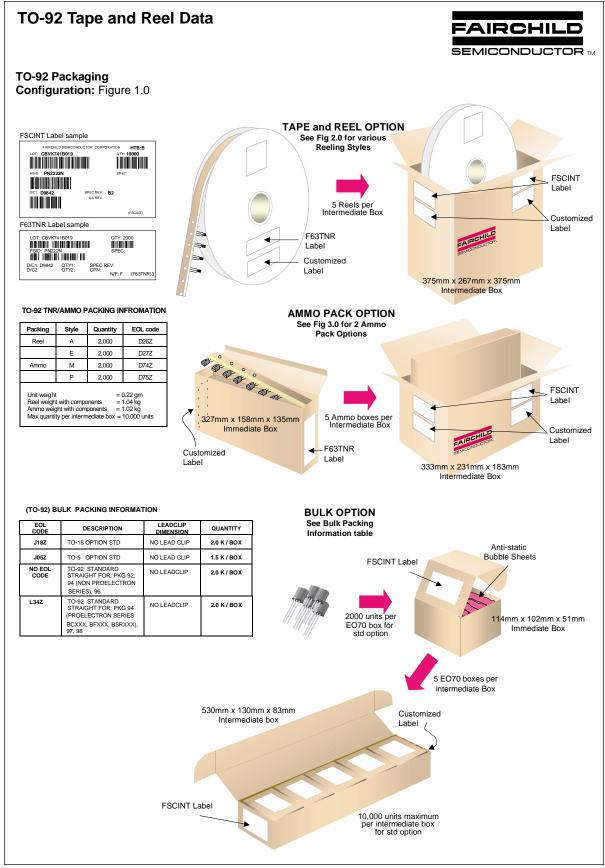
ON CHARACTERISTICS

h _{FE}	DC Current Gain	$ \begin{split} I_{C} &= 1.0 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 10 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 100 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 100 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ T_{A} &= -55^{\circ}\text{C} \\ I_{C} &= 500 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 1.0 \; \text{mA}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 10 \; \text{mA}, \; V_{CE} = 5.0 \; \text{V} \end{split} $	30 100 175 20 200 250	500 800	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{C} = 1.0 \text{ mA}, I_{B} = 0.1 \text{ mA}$		0.35	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 100 \ \mu A, \ V_{CE} = 5.0 \ V$	0.5	0.7	V

SMALL SIGNAL CHARACTERISTICS

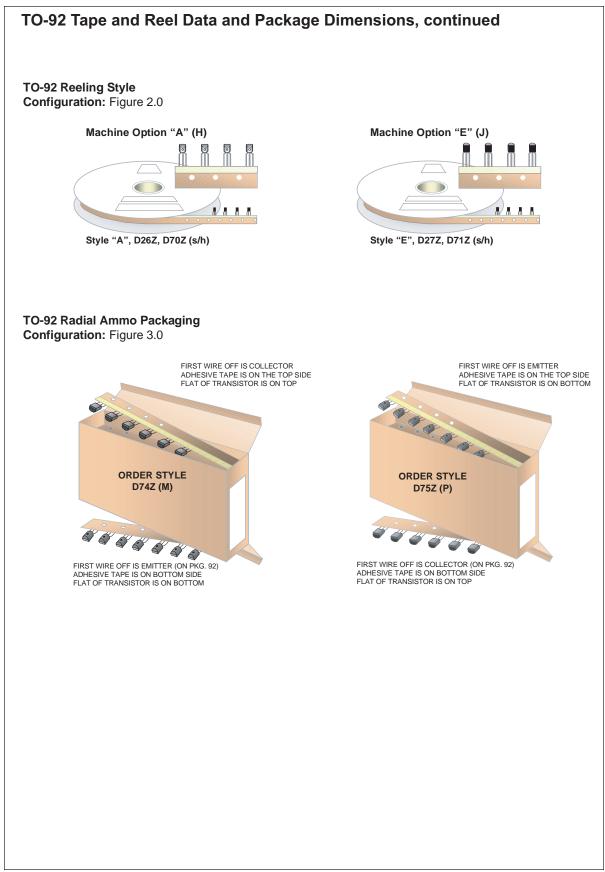
C _{obo}	Output Capacitance	V _{CB} =5.0 V, f = 140 kHz	6.0	pF
Cibo	Input Capacitance	V _{EB} = 0.5 V, f = 140 kHz	6.0	pF
NF	Noise Figure	$ I_{C} = 10 \ \mu \text{A}, \ V_{CE} = 5.0 \ \text{V}, \\ R_{S} = 10 \text{k}, \text{f} = 1.0 \ \text{kHz}, \text{BW} = 200 \ \text{Hz} $	3.0	dB

*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 3.0%

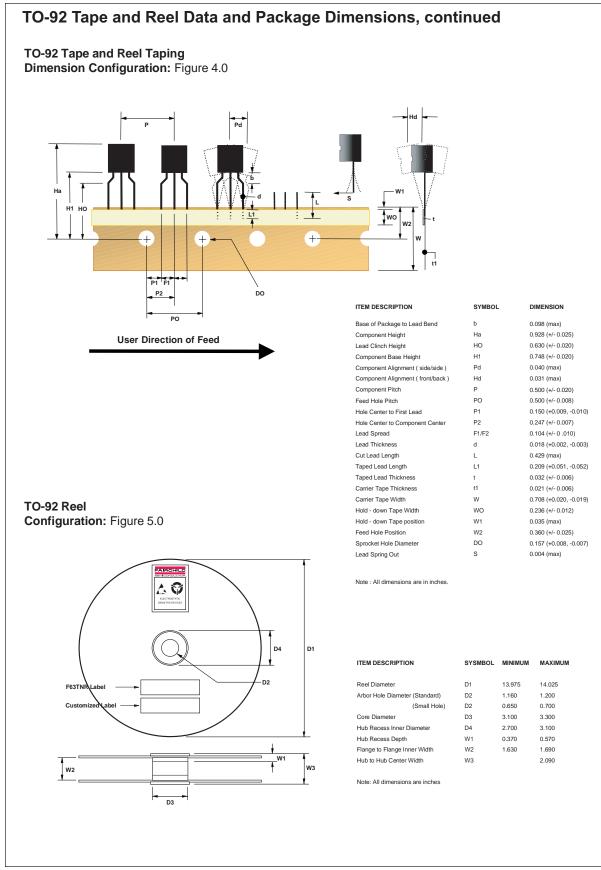


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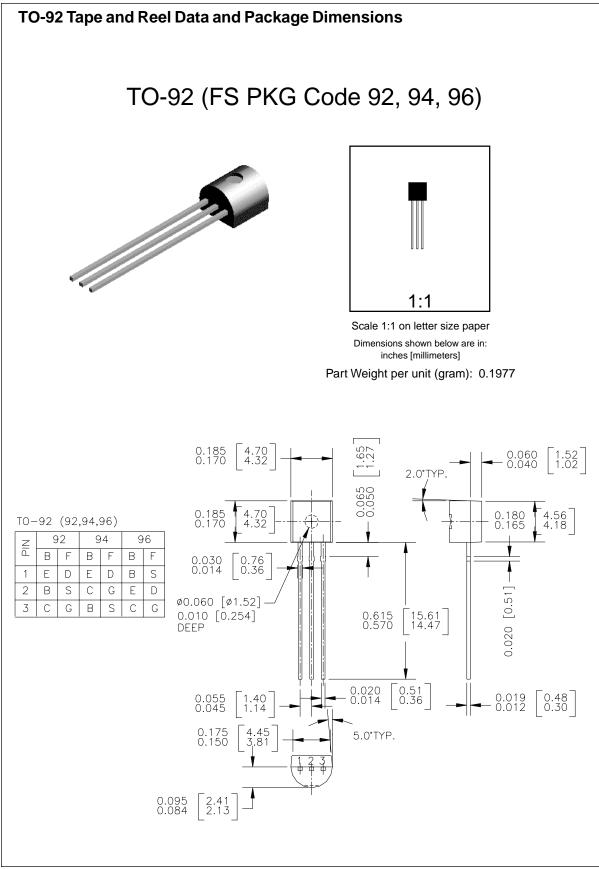
March 2001, Rev. B1



September 1999, Rev. B



July 1999, Rev. A



January 2000, Rev. B

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